



# 23<sup>rd</sup> ArbeitsKreis Bipolar (AKB)

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*Crolles, France, October 15, 2010*

<b>08:30 - 09:00</b>		<b>Arrival</b>		
<b>09:00 - 09:05</b>	<b>Opening</b>		<b>ST</b>	<b>D. Céli</b>
<b>09:05 - 09:30</b>	<b>Member matters Welcome to XMOD</b>		<b>IFX XMOD</b>	<b>J. Berkner B. Ardouin</b>
<b>09:30 - 10:05</b>	<b>Investigation of process variation on circuit's figures of merit</b>		<b>IMS</b>	<b>T. Zimmer</b>
<b>10:05 - 10:40</b>	<b>VBIC Models for high-speed and high-voltage HBTs in IHP's 0.13<math>\mu</math>m BiCMOS Technology</b>		<b>IHP</b>	<b>G. Fisher</b>
<b>10:40 - 11:10</b>		<b>Break</b>		
<b>11:10 - 11:50</b>	<b>What happens if VBIC fails in quasi-saturation?</b>		<b>IFX</b>	<b>J. Berkner</b>
<b>11:50 - 12:30</b>	<b>Schottky barrier diode modeling using VBIC</b>		<b>AMS</b>	<b>B. Senapati</b>
<b>12:30 - 13:10</b>	<b>Revisiting the charge concept in HBT/BJT models</b>		<b>AMS</b>	<b>Z. Huszka</b>
<b>13:10 - 14:30</b>		<b>Lunch</b>		
<b>14:30 - 15:10</b>	<b>How to avoid HICUM/L2 v2.24 traps?</b>		<b>ST</b>	<b>D. Céli</b>
<b>15:10 - 15:50</b>	<b>Application of HICUM/L2 v2.30 to advanced multi-100GHz HBTs</b>		<b>TuD</b>	<b>A. Pawlak</b>
<b>15:50 - 16:20</b>	<b>Modeling Darlington Transistors</b>		<b>NXP</b>	<b>J. Wilhlemi</b>
<b>16:20 - 16:50</b>		<b>Break</b>		
<b>16:50 - 17:30</b>	<b>On the feasibility of single touch on wafer calibration using HBT</b>		<b>FHWS</b>	<b>P. Baureis</b>
<b>17:30 - 17:50</b>	<b>Limitations of Bipolar compact models for LF noise. Part II - Answers to HICUM WS remarks</b>		<b>ST</b>	<b>N. Derrier</b>